An SOI wafer produced by the method according to Claim 5, which has an RMS value of 0.5 nm or less concerning surface roughness for both of 1 μm square and 10 μm square. --

## **REMARKS**

Claims 1-9 are pending. By this Preliminary Amendment, claim 6 is amended to remove multiple dependencies. Claims 7-9 are added to compensate for the material deleted from claim 6. Prompt and favorable examination on the merits is respectfully requested.

The attached Appendix includes marked-up copies of each rewritten claim (37 C.F.R. 1.121(c)(1)(ii)).

Respectfully submitted,

William P. Berridge Registration No. 30,024

Thomas J. Pardini Registration No. 30,411

WPB:TJP/cmm

Attachment:

Appendix

Date: June 11, 2001

OLIFF & BERRIDGE, PLC P.O. Box 19928 Alexandria, Virginia 22320 Telephone: (703) 836-6400 DEPOSIT ACCOUNT USE
AUTHORIZATION
Please grant any extension
necessary for entry;
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## **APPENDIX**

Changes to Claims:

Claims 7-9 are added.

The following is a marked-up version of the amended claim:

6. (Amended) An SOI wafer produced by the method according to any one of Claims 1-3 and 5, Claim 1, which has an RMS value of 0.5 nm or less concerning surface roughness for both of 1  $\mu$ m square and 10  $\mu$ m square.